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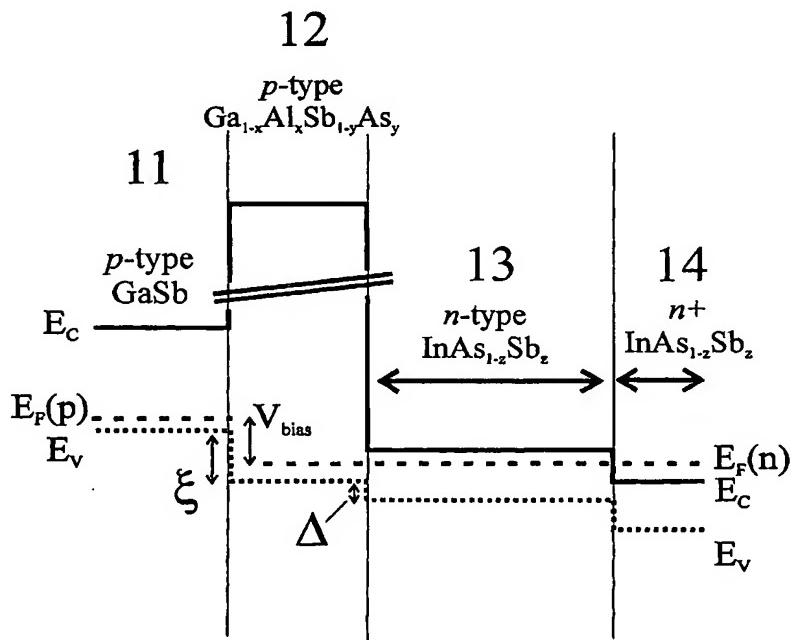
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(54) Title: DEPLETION-LESS PHOTODIODE WITH SUPPRESSED DARK CURRENT AND METHOD FOR PRODUCING THE SAME



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(57) Abstract: The invention relates to a photo-detector with a reduced G-R noise, which comprises a sequence of a p-type contact layer, a middle barrier layer and an n-type photon absorbing layer, wherein the middle barrier layer has an energy bandgap significantly greater than that of the photon absorbing layer, and there is no layer with a narrower energy bandgap than that in the photon-absorbing layer.



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